

isc Silicon NPN Power Transistor

NJW21194G

2

2.Collector 3.Emitter

TO-3PN Package

G

R

MAX 20.30

15 70

4.90

1.10

2.10

3.60

3.20

3.40

0.605

20.70

.20

5.10

3.45

2,100

6.20

PIN: 1.Base

С

DESCRIPTION · Large collector current · Low collector saturation voltage · High power dissipation · Minimum Lot-to-Lot variations for robust device performance and reliable operation 1 2 3 **APPLICATIONS** · Designed for use in DC-DC converter · Driver of solenoid or motor · For audio amplifier applications ABSOLUTE MAXIMUM RATINGS(Ta=25℃) Ó SYMBOL UNIT PARAMETER VALUE 400 VCBO Collector-Base Voltage V 250 VCEO Collector-Emitter Voltage V V VEBO **Emitter-Base Voltage** 5 mm Collector Current-Continuous lc 30 А DIM MIN A 19.60 15.50 **Base Current** 5 В I_B А 4.70 C D 0.90 Pc Collector Power Dissipation@Tc=25°C 200 W E 1.90 F 3.40°C ТJ **Junction Temperature** -65~150 G 2.90Н 3.20J 0.595 -65~150 °C Storage Temperature Tstg ĸ 19.80 1.90 N 10.89 THERMAL CHARACTERISTICS 4.90 Q 3.35 R SYMBOL PARAMETER MAX UNIT 1.995 S U 5.90 Rth j-c Thermal Resistance, Junction to Case 0.625 °C/W Y 9.90 | 10.10

isc website: www.iscsemi.com

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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|------------------------|--------------------------------------|--|-----|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 30mA; I _B = 0 | 250 | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 1mA; I _E = 0 | 400 | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA; I _C = 0 | 5.0 | | V |
| V _{CE(sat)-1} | Collector-Emitter Saturation Voltage | I _C =8A; I _B = 0.8A | | 1.4 | V |
| V _{CE(sat)-2} | Collector-Emitter Saturation Voltage | I _C =16A; I _B = 3.2A | | 4.0 | V |
| V _{BE} (on) | Base-Emitter On Voltage | I _C =8A; V _{CE} = 5V | | 2.2 | V |
| Iceo | Collector Cutoff Current | V _{CE} = 250V; I _B =0 | | 0.1 | mA |
| I _{Сво} | Collector Cutoff Current | V _{CB} = 400V; I _E =0 | | 0.1 | mA |
| h _{FE-1} | DC Current Gain | I _C = 8A; V _{CE} = 5V | 20 | 80 | |
| h _{FE-2} | DC Current Gain | I _C = 16A; V _{CE} = 5V | 8 | | |

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